

What is claimed is:

1. A semiconductor device comprising:
a substrate having a region to be irradiated
with radiating rays, and
5 a metal wring layer located on the substrate
one of directly and indirectly,
wherein the metal wring layer is made of a
light metal,
and wherein the metal wring layer located on
10 the region to be irradiated with radiating rays is formed
thinner than that formed on regions except for the region
to be irradiated so as to reach the radiating rays to the
region to be irradiated.
- 15 2. The semiconductor device in accordance with
claim 1, wherein none of the metal wring layer is located
on the region to be irradiated.
- 20 3. The semiconductor device in accordance with
claim 2, wherein an insulation layer is located on the
region to be irradiated.
- 25 4. The semiconductor device in accordance with
claim 3, wherein the metal wring layer located on the
regions except for the region to be irradiated is formed
in a thickness so as not to provide any adverse effect on

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the regions except for the region to be irradiated.

5. A semiconductor device comprising:

a substrate having a region to be irradiated
5 with radiating rays, and

a metal wiring layer located on the substrate,
wherein the metal wiring layer is made of a
light metal,

and the metal wiring layer is used as a mask for
10 restricting penetration of the radiating rays into
regions except for the region to be irradiated.

6. The semiconductor device in accordance with
claim 5, the semiconductor device is an insulated gate
15 bipolar transistor, and wherein the region to be
irradiated is a positive-negative junction region where a
parasitic diode is generated.

7. The semiconductor device in accordance with
20 claim 5, wherein the semiconductor device is a metal
oxide semiconductor field effect transistor, and wherein
the region to be irradiated is a positive-negative
junction region where a parasitic diode is generated.

8. A method for manufacturing a semiconductor
25 device having a substrate, and a metal wiring layer

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located on the substrate, a region of the substrate being irradiated with radiating rays, the method comprising the steps of:

- entirely forming the metal wiring layer,
- 5 removing the metal wiring layer located on the region to be irradiated, and
- radiating the radiating rays using the metal wiring layer being remained as a mask.

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